

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
B _V DSS Drain–Source Breakdown Voltage	V _{GS} = 0 I _D = 10mA	40			V
I _D DSS Zero Gate Voltage Drain Current	V _{DS} = 12.5V V _{GS} = 0			1	mA
I _G DSS Gate Leakage Current	V _{GS} = 20V V _{DS} = 0			1	μA
V _{GS(th)} Gate Threshold Voltage*	I _D = 10mA V _{DS} = V _{GS}	1		7	V
g _{fs} Forward Transconductance*	V _{DS} = 10V I _D = 0.2A	0.18			S
G _{PS} Common Source Power Gain	P _O = 2.5W	10			dB
η Drain Efficiency	V _{DS} = 12.5V I _{DQ} = 0.1A	40			%
VSWR Load Mismatch Tolerance	f = 1GHz	20:1			—
C _{iss} Input Capacitance	V _{DS} = 0 V _{GS} = -5V f = 1MHz			12	pF
C _{oss} Output Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz			10	pF
C _{rss} Reverse Transfer Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz			1	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 10°C / W
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